

MOSFET - Power, Single N-Channel, SUPERFET® V, FAST, TO220

600 V, 185 mΩ, 15 A

NTP185N60S5H

Description

The SUPERFET V MOSFET FAST series helps maximize system efficiency by the extremely low switching losses in hard switching application.

Features

- 650 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 148\text{ m}\Omega$
- 100% Avalanche Tested
- Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Telecom / Server Power Supplies
- EV Charger / UPS / Solar / Industrial Power Supplies

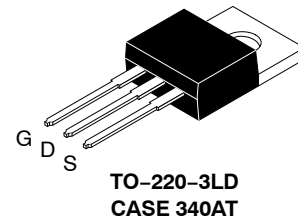
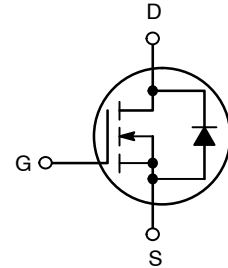
ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$, Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	600	V
Gate-to-Source Voltage	V_{GSS}	DC	± 30
		AC ($f > 1\text{ Hz}$)	± 30
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	15
		$T_C = 100^\circ\text{C}$	9
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	116
Pulsed Drain Current (Note 1)	$T_C = 25^\circ\text{C}$	I_{DM}	53
Pulsed Source Current (Body Diode) (Note 1)	$T_C = 25^\circ\text{C}$	I_{SM}	53
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)	I_S	15	A
Single Pulse Avalanche Energy	$I_L = 3.6\text{ A}, R_G = 25\ \Omega$	E_{AS}	124
Avalanche Current	I_{AS}	3.6	A
Repetitive Avalanche Energy (Note 1)	E_{AR}	1.16	mJ
MOSFET dv/dt	dv/dt	120	V/ns
Peak Diode Recovery dv/dt (Note 2)		20	
Lead Temperature for Soldering Purposes (1/8" from case for 10 seconds)	T_L	260	$^\circ\text{C}$

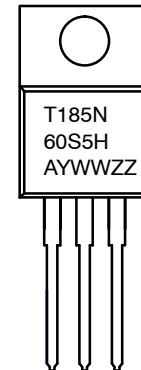
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $I_{SD} \leq 7.5\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq 400\text{ V}$, starting $T_J = 25^\circ\text{C}$.

V_{DSS}	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
600 V	185 mΩ @ 10 V	15 A



MARKING DIAGRAM



T185N60S5H = Specific Device Code
A = Assembly Plant Code
YWW = Date Code (Year & Week)
ZZ = Lot

ORDERING INFORMATION

Device	Package	Shipping
NTP185N60S5H	TO220	50 Units / Tube

NTP185N60S5H

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case, Max.	$R_{\theta JC}$	1.08	°C/W
Thermal Resistance, Junction-to-Ambient, Max.	$R_{\theta JA}$	62.5	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	$V_{(BR)DSS}$	600	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, Referenced to 25°C	$\Delta V_{(BR)DSS} / \Delta T_J$	-	630	-	mV/°C
Zero Gate Voltage Drain Current	$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}, T_J = 25^\circ\text{C}$	I_{DSS}	-	-	1	μA
Gate-to-Source Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	-	-	±100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 7.5\text{ A}, T_J = 25^\circ\text{C}$	$R_{DS(on)}$	-	148	185	mΩ
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1.4\text{ mA}, T_J = 25^\circ\text{C}$	$V_{GS(th)}$	2.7	-	4.3	V
Forward Trans-conductance	$V_{DS} = 20\text{ V}, I_D = 7.5\text{ A}$	g_{FS}	-	18	-	S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 250\text{ kHz}$	C_{ISS}	-	1350	-	pF
Output Capacitance		C_{OSS}	-	25	-	
Time Related Output Capacitance	$I_D = \text{Constant}, V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	$C_{OSS(tr.)}$	-	372	-	
Energy Related Output Capacitance		$C_{OSS(er.)}$	-	42	-	
Total Gate Charge	$V_{DD} = 400\text{ V}, I_D = 7.5\text{ A}, V_{GS} = 10\text{ V}$	$Q_{G(tot)}$	-	25	-	nC
Gate-to-Source Charge		Q_{GS}	-	7	-	
Gate-to-Drain Charge		Q_{GD}	-	8	-	
Gate Resistance	$f = 1\text{ MHz}$	R_G	-	0.9	-	Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$V_{GS} = 0/10\text{ V}, V_{DD} = 400\text{ V}, I_D = 7.5\text{ A}, R_G = 10\ \Omega$	$t_{d(on)}$	-	18	-	ns
Rise Time		t_r	-	9	-	
Turn-Off Delay Time		$t_{d(off)}$	-	53	-	
Fall Time		t_f	-	4	-	

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{GS} = 0\text{ V}, I_{SD} = 7.5\text{ A}, T_J = 25^\circ\text{C}$	V_{SD}	-	-	1.2	V
Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_{SD} = 7.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_{DD} = 400\text{ V}$	t_{RR}	-	251	-	ns
Reverse Recovery Charge		Q_{RR}	-	3028	-	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

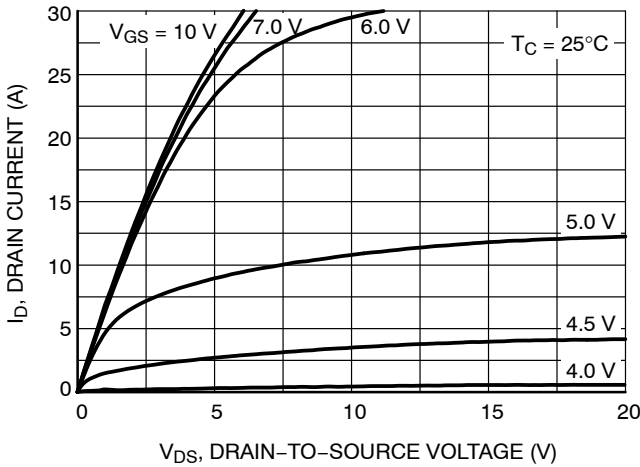


Figure 1. On-Region Characteristics

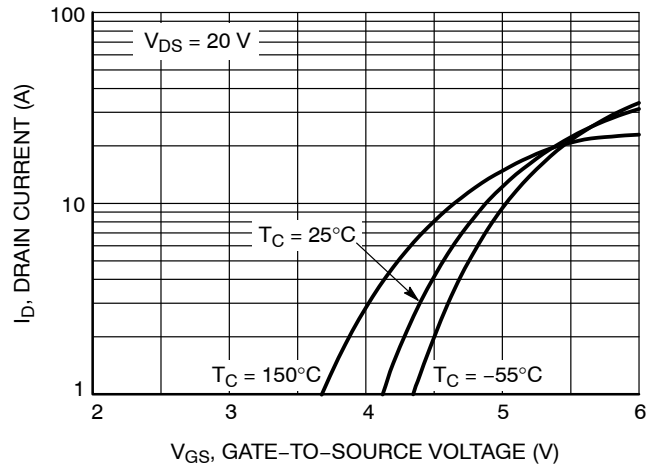


Figure 2. Transfer Characteristics

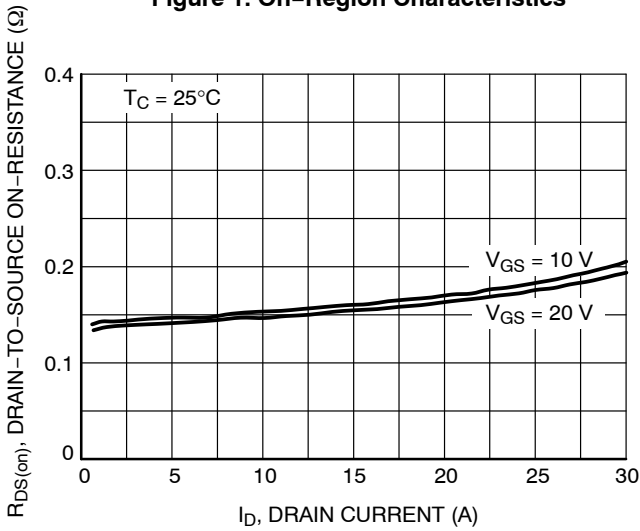


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

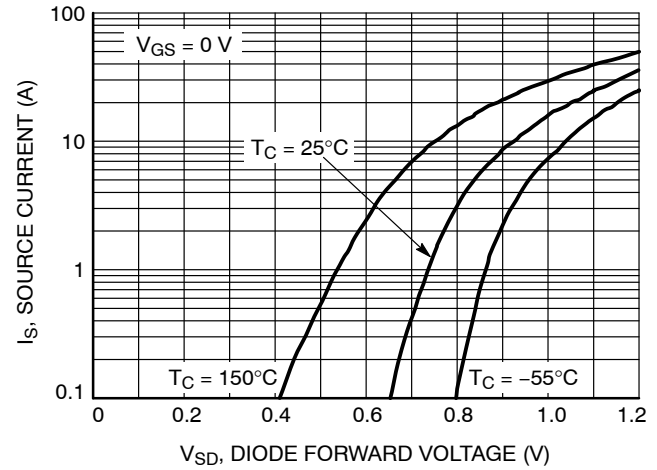


Figure 4. Diode Forward Voltage vs. Source Current

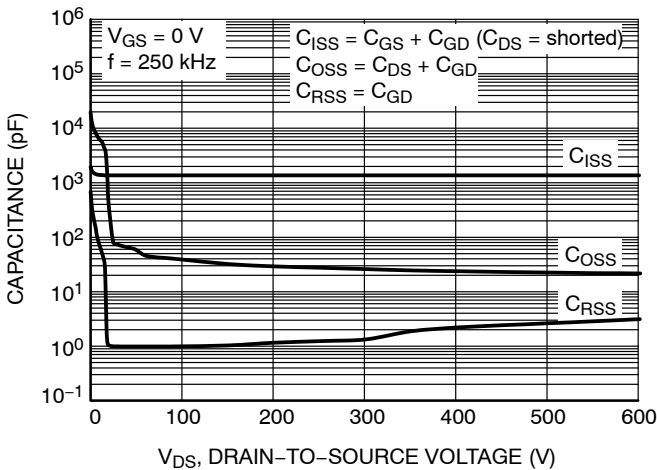


Figure 5. Capacitance Characteristics

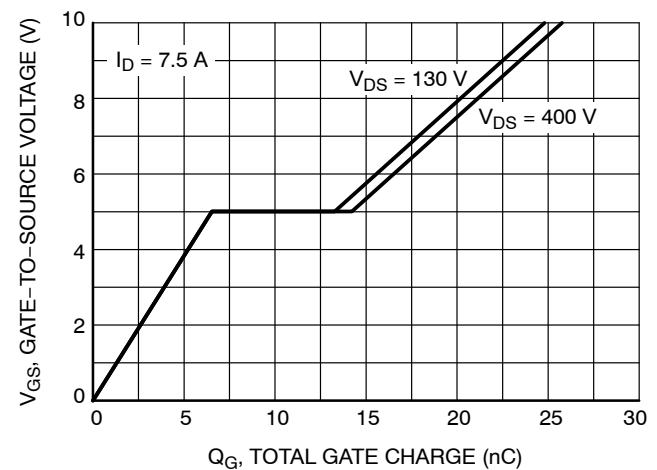


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS

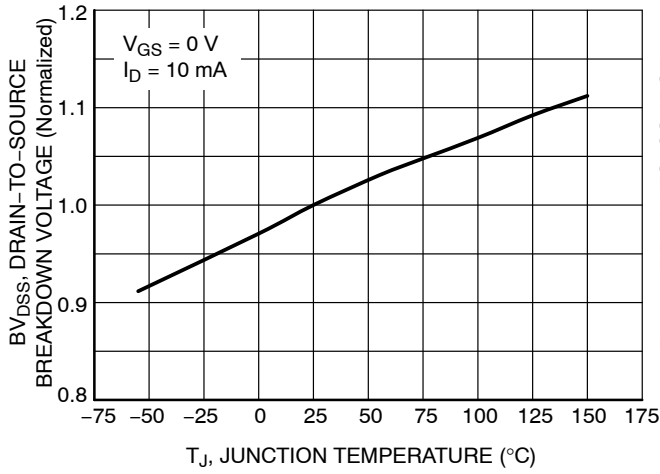


Figure 7. Breakdown Voltage Variation vs. Temperature

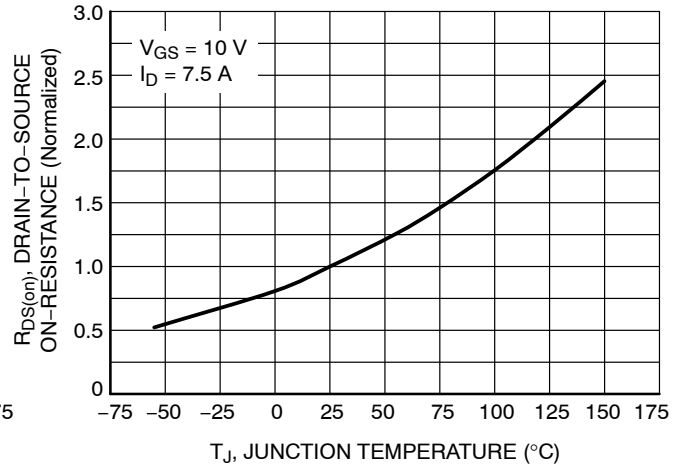


Figure 8. On-Resistance Variation vs. Temperature

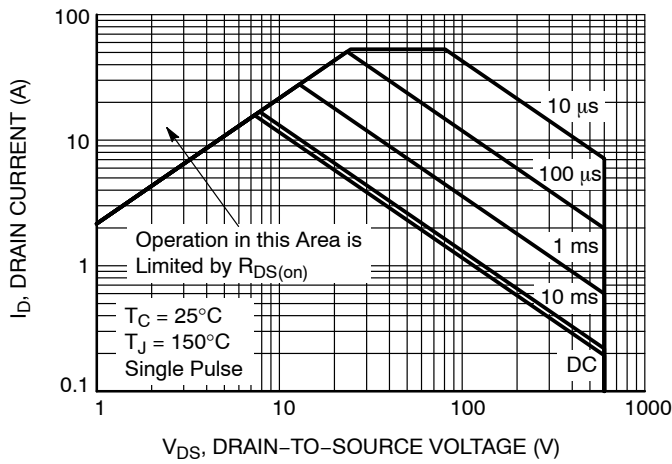


Figure 9. Maximum Safe Operating Area

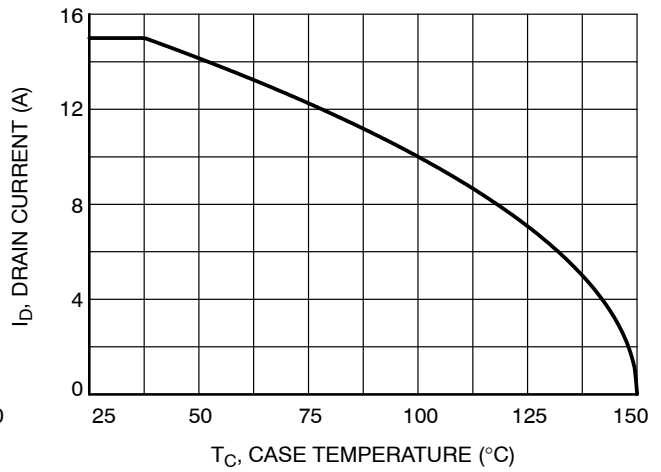


Figure 10. Maximum Drain Current vs. Case Temperature

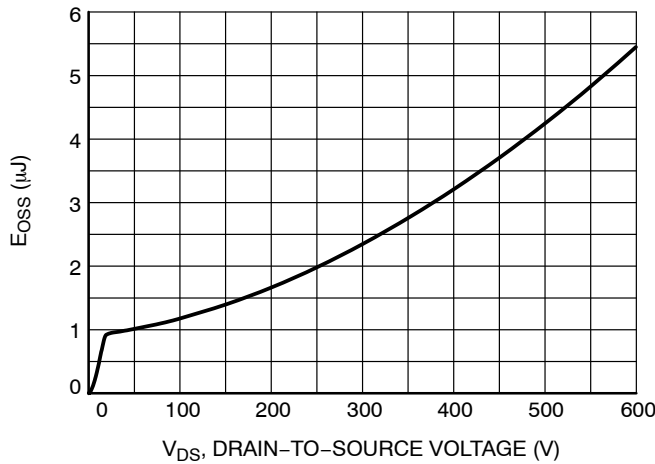


Figure 11. E_{OSS} vs. Drain-to-Source Voltage

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TYPICAL CHARACTERISTICS

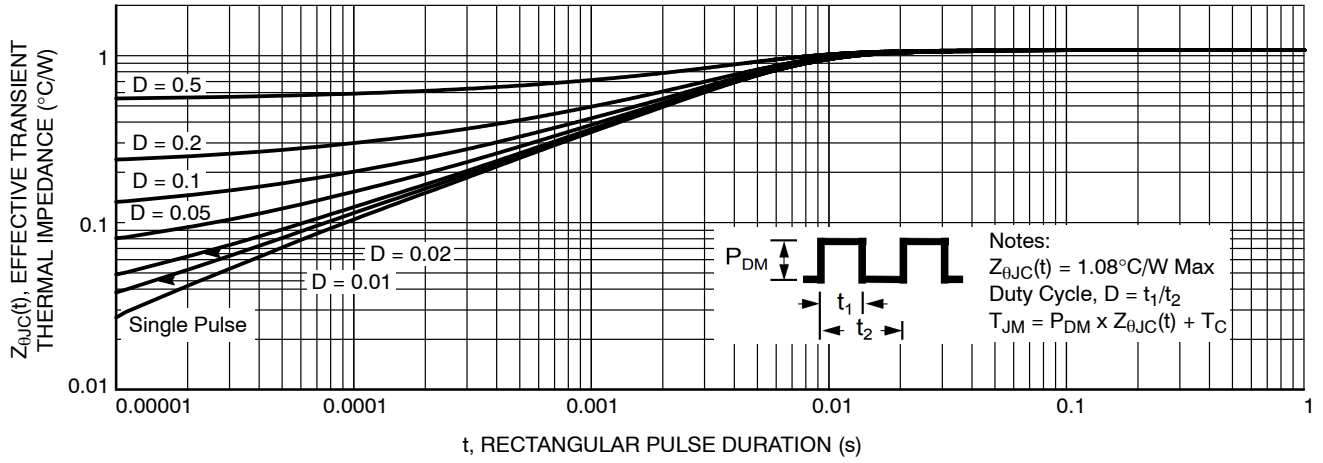


Figure 12. Transient Thermal Impedance

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Figure 13. Gate Charge Test Circuit & Waveform

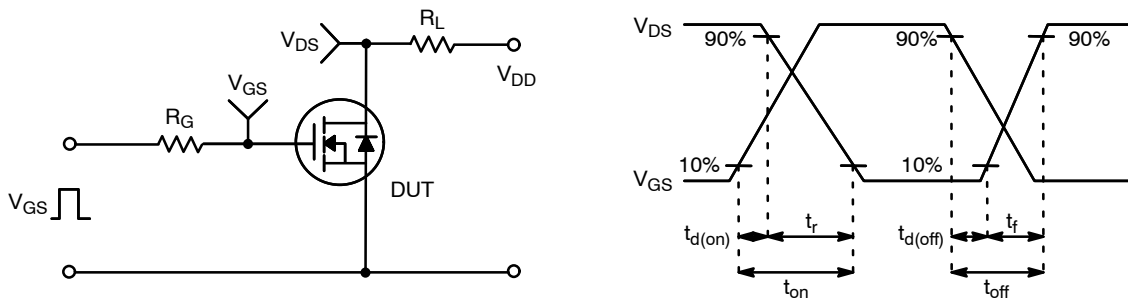


Figure 14. Resistive Switching Test Circuit & Waveforms

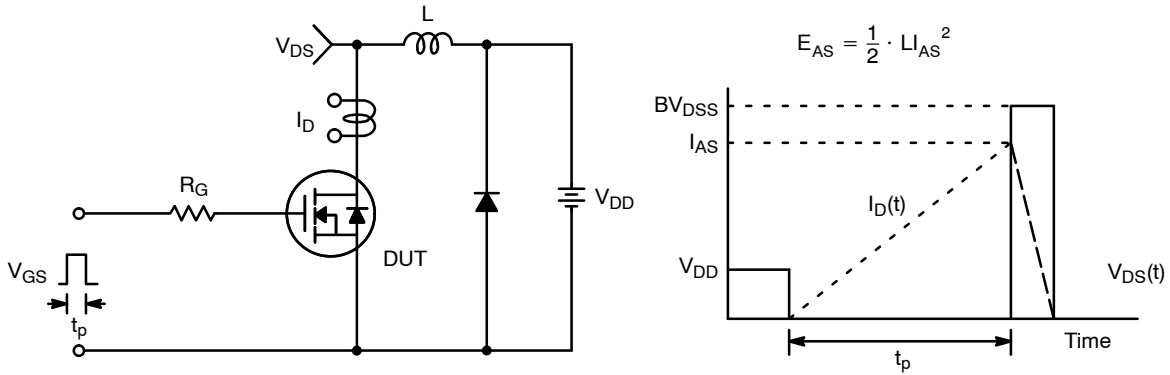


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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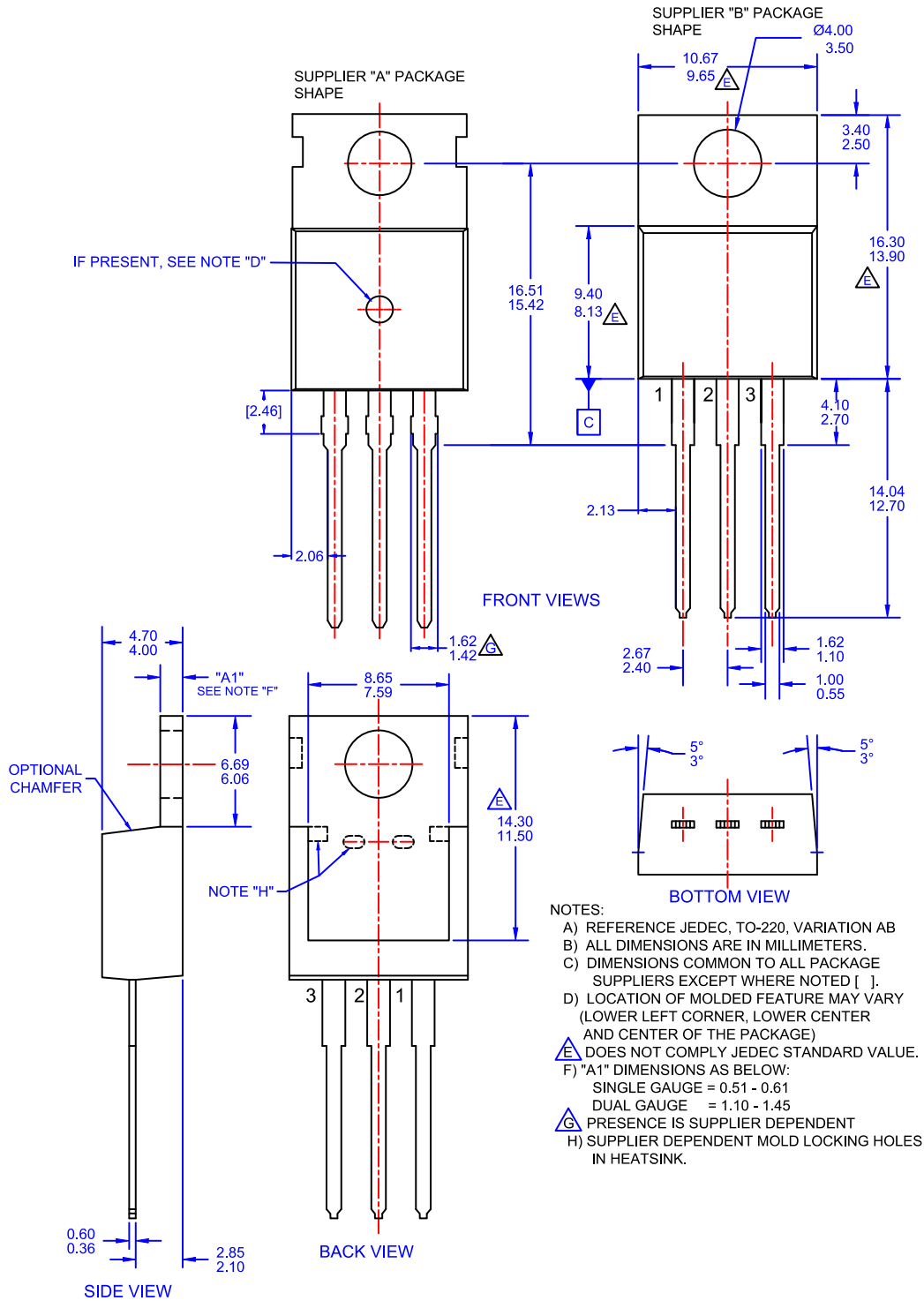


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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PACKAGE DIMENSIONS

TO-220-3LD
CASE 340AT
ISSUE A



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